

## High-reliability discrete products and engineering services since 1977

## C35 SERIES

### SILICON CONTROLLED RECTIFIER

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak repetitive forward and reverse blocking voltage <sup>(1)</sup>			
$(T_c = -65 \text{ to } +125^{\circ}\text{C})$			
C35U		25	
C35F		50	
C35A		100	Volts
C35G		150	
C35B	V <sub>DRM</sub> or V <sub>RRM</sub>	200	
C35H	V DRM OI V RRM	250	VOICS
C35C		300	
C35D		400	
C35E		500	
C35M		600	
C35S		700	
C35N		800	
Non-repetitive peak reverse voltage			
(T <sub>C</sub> = -65 to +125°C, V < 5.0ms)			
C35U		35	Volts
C35F		75	
C35A		150	
C35G		225	
C35B	$V_{RSM}$	300	
C35H	10.11	350	
C35C		400	
C35D		500	
C35E		600	
C35M		720	
C35S		840	
C35N		960	
Forward current RMS (all conduction angles)	I <sub>T(RMS)</sub>	35	Amps
Peak non-repetitive surge current (1cycle, 60 Hz)	I <sub>TSM</sub>	225	Amps
Circuit fusing considerations (t = 8.3ms)	l²t	75	A <sup>2</sup> s
Forward peak gate power	P <sub>GM</sub>	5	Watts
Forward average gate power	P <sub>G(AV)</sub>	0.5	Watts
Peak reverse gate voltage	$V_{GRM}$	5	Volts
Operating junction temperature range	T <sub>J</sub>	-65 to +125	°C
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C



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#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R <sub>eJC</sub>	1.7	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>c</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
Peak reverse or forward blocking current					
$(V_D = Rated V_{DRM}, T_C = 125^{\circ}C)$					
$(V_R = Rated V_{RRM}, T_C = 125^{\circ}C)$					
C35U,F, A, G		-	-	13	
C35B		-	-	12	
C35H	I <sub>DRM</sub> or	-	-	11	
C35C	I <sub>RRM</sub>	-	-	10	mA
C35D		-	-	8	
C35E		-	-	6	
C35M		-	-	5	
C35S		-	-	4.5	
C35N		-	-	4	
Average forward or reverse blocking current					
$(V_D = Rated V_{DRM}, T_C = 125^{\circ}C)$					
$(V_R = Rated V_{RRM}, T_C = 125^{\circ}C)$					
C35U,F, A, G		-	-	6.5	
C35B		-	-	6	
C35H	I <sub>DRM(AV)</sub> or	-	-	5.5	
C35C	I <sub>RRM(AV)</sub>	-	-	5	mA
C35D		-	-	4	İ
C35E		-	-	3	
C35M		-	-	2.5	
C35S		-	-	2.25	
C35N		-	-	2	
Peak on-state voltage	V <sub>TM</sub>				Volts
$(I_{TM} = 50.3A \text{ peak, pulse width} \le 1 \text{ms, duty cycle} \le 2.0\%)$	VTM	-	-	2	VOILS
Gate trigger current (continuous dc)					
$(V_D = 12V, R_L = 50\Omega)$	I <sub>GT</sub>	-	6	40	mA
$(V_D = 12V, R_L = 50\Omega, T_C = -65^{\circ}C)$		-	-	80	
Gate trigger voltage (continuous dc)					
$(V_D = 12V, R_L = 50\Omega, T_C = -65^{\circ}C \text{ to } +125^{\circ}C)$	$V_{GT}$	-	-	3	Volts
$(V_D = Rated V_{DRM}, R_L = 1000\Omega, T_C = 125^{\circ}C)$		0.25	-	-	
Holding current					A
(V <sub>D</sub> = 24V, gate supply = 10V, 20 $\Omega$ , 45 $\mu$ s minimum pulse width, I <sub>T</sub> = 0.5A)	I <sub>H</sub>	-	-	100	mA
Critical rate of rise of forward blocking voltage					
$(V_D = Rated V_{DRM}, T_C = 125$ °C)					
C35U, F, M, S, N	dv/dt	10	-	-	V/µs
C35A, G, B, H		20	-	-	
C35C, D, E		25	-	-	



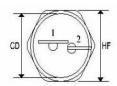
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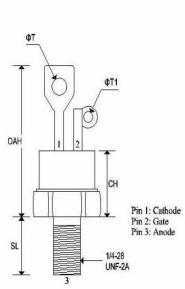
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#### MECHANICAL CHARACTERISTICS

Case	TO-48
Marking	Body painted, alpha-numeric
Polarity	Cathode is stud





	TO-48				
	Inches		Millin	imeters	
	Min	Max	Min	Max	
CD	4	0.543	P	13.793	
CH	2	0.550	-	13.970	
HF	0.544	0.563	13.817	14.301	
OAH	-	1.193	-	30.303	
SL	0.422	0.453	10.718	11.507	
ΦТ	0.125	0.165	3.175	4.191	
ΦT <sub>1</sub>	0.060	0.075	1.524	1.905	

